ESD6V8WT

SILICON EPITAXIAL PLANAR DIODE

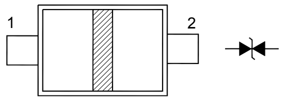
ESD protection diode

Features

- Ultra small mold type
- Bi-direction high reliability

PINNING

PIN	DESCRIPTION
1	Anode
2	Anode



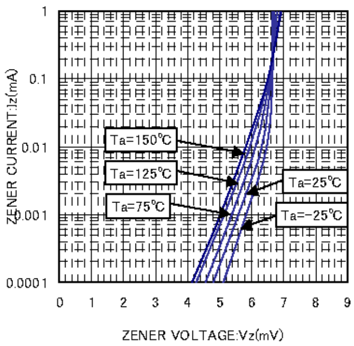
Top View
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings (T_a = 25℃)

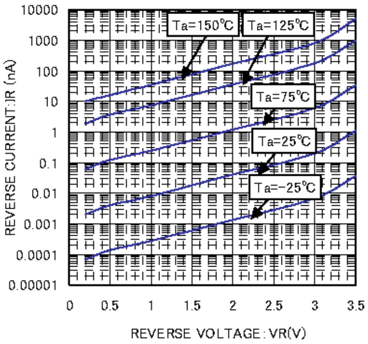
Parameter	Symbol	Value	Unit
Peak Pulse Power (tp = 10 X 1000 µs)	P_{PK}	10	W
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	- 55 to + 150	℃
Operation Temperature Range	T_{opr}	- 55 to + 150	℃

Characteristics at T_a = 25℃

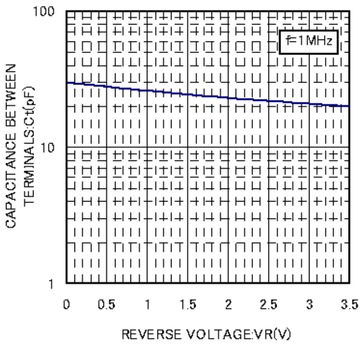
Parameter	Symbol	Min.	Typ.	Max.	Unit
Zener Voltage at I_Z = 1 mA	V_Z	5.78	-	7.82	V
Reverse Current at V_R = 3.5 V	I_R	-	-	0.5	µA
Capacitance between Terminals at V_R = 0 V, f = 1 MHz	C_T	-	30	-	pF



Vz−Iz CHARACTERISTICS



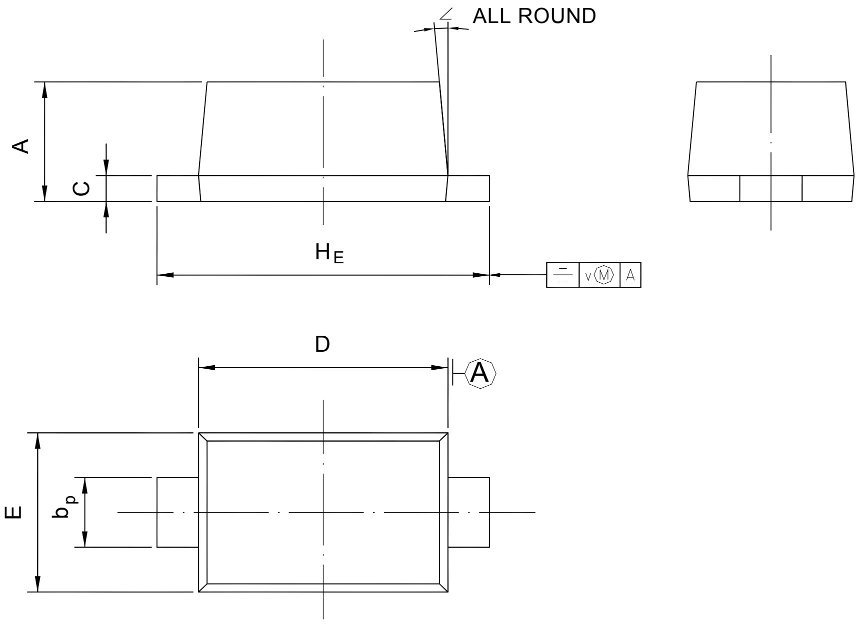
VR−IR CHARACTERISTICS



VR−Ct CHARACTERISTICS

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°